

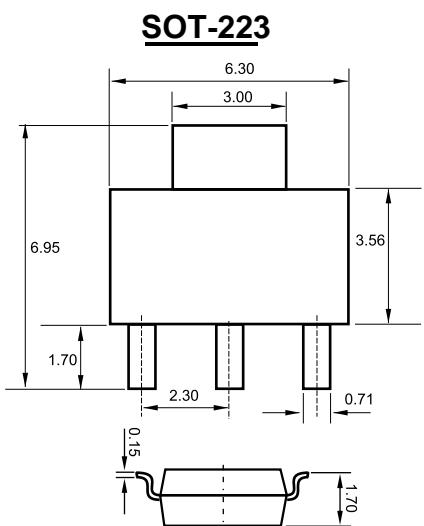
1. BASE
2. COLLECTOR
3. Emitter

## Features

- ✧ Epitaxial planar die construction
- ✧ Complementary PNP Type available (PZT2907A)

### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	75	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	600	mA
$P_c$	Collector Power Dissipation	1	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55 to +150	$^\circ\text{C}$



Dimensions in inches and (millimeters)

### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C= 10\mu\text{A}, I_E=0$	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C= 10\text{mA}, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=60\text{V}, I_E=0$		10	nA
Collector cut-off current	$I_{CEX}$	$V_{CE}=60\text{V}, V_{BE(\text{off})}=3\text{V}$		10	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}= 3\text{V} , I_C=0$		10	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C= 0.1\text{mA}$	35		
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C= 1\text{mA}$	50		
	$h_{FE(3)}$	$V_{CE}=10\text{V}, I_C= 10\text{mA}$	75		
	$h_{FE(4)}$	$V_{CE}=10\text{V}, I_C= 150\text{mA}$	100	300	
	$h_{FE(5)}$	$V_{CE}=1\text{V}, I_C= 150\text{mA}$	50		
	$h_{FE(6)}$	$V_{CE}=10\text{V}, I_C= 500\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C=500\text{mA}, I_B= 50\text{mA}$		1	V
	$V_{CE(\text{sat})}$	$I_C=150\text{mA}, I_B= 15\text{mA}$		0.3	V
Base-emitter saturation voltage	$V_{BE(\text{sat})}$	$I_C=500\text{mA}, I_B= 50\text{mA}$		2.0	V
	$V_{BE(\text{sat})}$	$I_C=150\text{mA}, I_B=15\text{mA}$		1.2	V
Transition frequency	$f_T$	$V_{CE}=20\text{V}, I_C= 20\text{mA}, f=100\text{MHz}$	300		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10\text{V}, I_E= 0, f=1\text{MHz}$		8	pF
Delay time	$t_d$	$V_{CC}=30\text{V}, I_C=150\text{mA}$ $V_{BE(\text{off})}=0.5\text{V}, I_B=15\text{mA}$		10	nS
Rise time	$t_r$			25	nS
Storage time	$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}$ $I_B=-I_{B2}= 15\text{mA}$		225	nS
Fall time	$t_f$			60	nS

## Typical characteristics

